

<b>SANYO</b>	No.5297A	<b>2SJ383</b>
		P-Channel MOS Silicon FET

**Ultrahigh-Speed Switching Applications**

**Features**

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

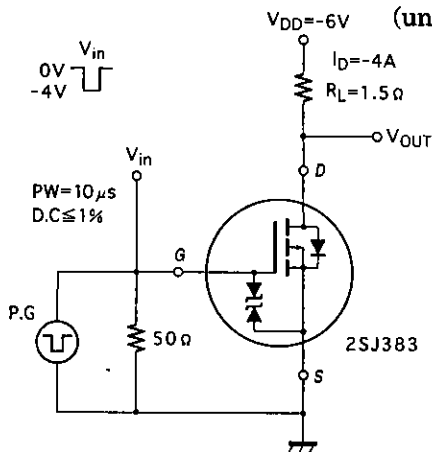
**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain-to-Source Voltage	$V_{DSS}$	-12	V
Gate-to-Source Voltage	$V_{GSS}$	±10	V
Drain Current (DC)	$I_D$	-8	A
Drain Current (Pulse)	$I_{DP}$	-32	A
Allowable Power Dissipation	$P_D$	1.0	W
		$T_c = 25^\circ\text{C}$	
		30	W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

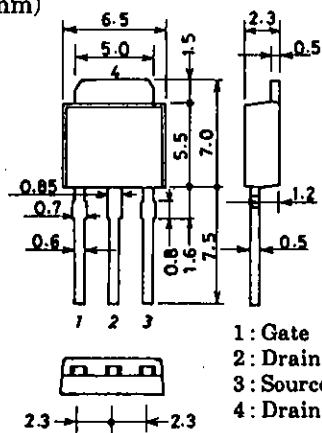
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-12			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -10\text{V}, V_{GS} = 0$			-100	µA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 8\text{V}, V_{DS} = 0$			±10	µA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -6\text{V}, I_D = -1\text{mA}$	-0.4		-1.4	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -6\text{V}, I_D = -4\text{A}$	6	8		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -4\text{A}, V_{GS} = -4\text{V}$		65	82	mΩ
	$R_{DS(on)}$	$I_D = -2\text{A}, V_{GS} = -2.5\text{V}$		90	144	mΩ
Input Capacitance	$C_{iss}$	$V_{DS} = -6\text{V}, f = 1\text{MHz}$		1000		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -6\text{V}, f = 1\text{MHz}$		800		pF
Reverse Transfer Capacitance	$C_{res}$	$V_{DS} = -6\text{V}, f = 1\text{MHz}$		270		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		25		ns
Rise Time	$t_r$	"		170		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		180		ns
Fall Time	$t_f$	"		270		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -8\text{A}, V_{GS} = 0$	-1.0	-1.2		V

**Switching Time Test Circuit**



**Package Dimensions 2083B**

(unit: mm)

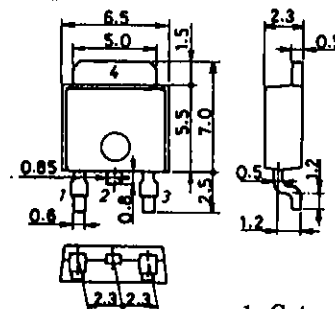


- 1: Gate
- 2: Drain
- 3: Source
- 4: Drain

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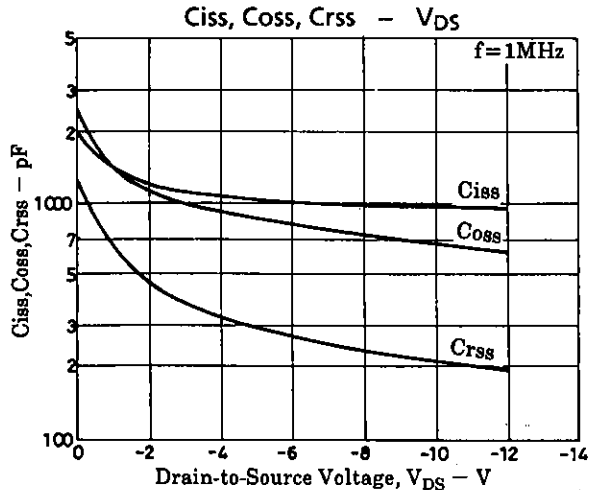
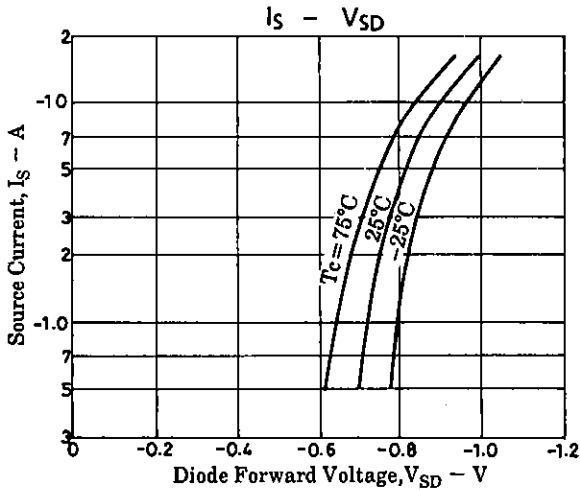
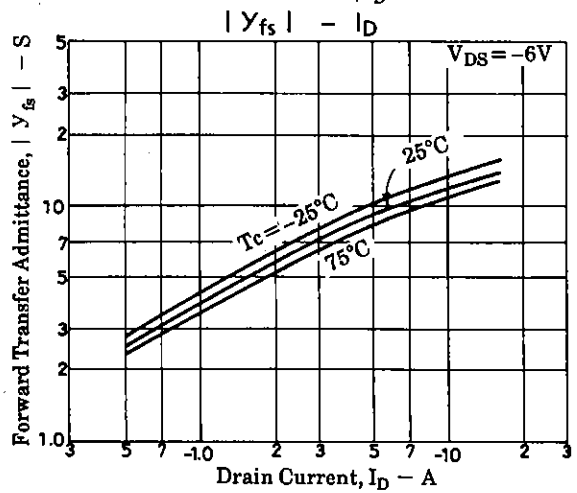
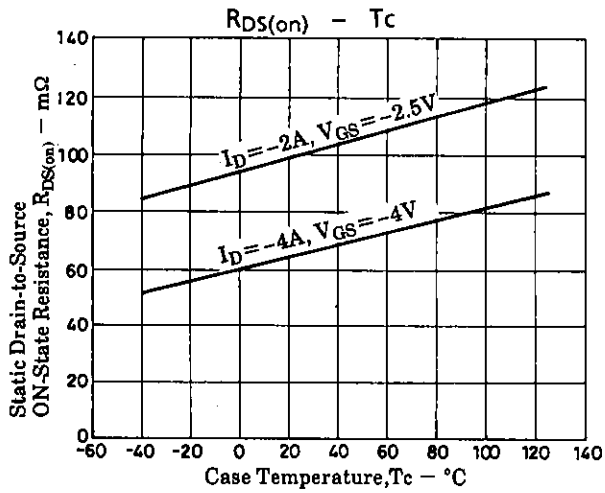
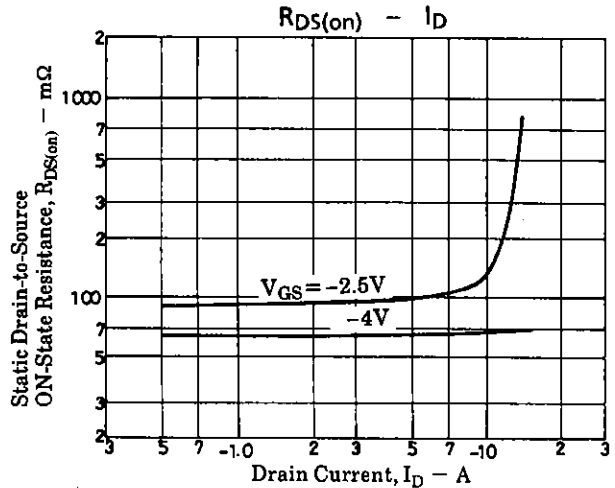
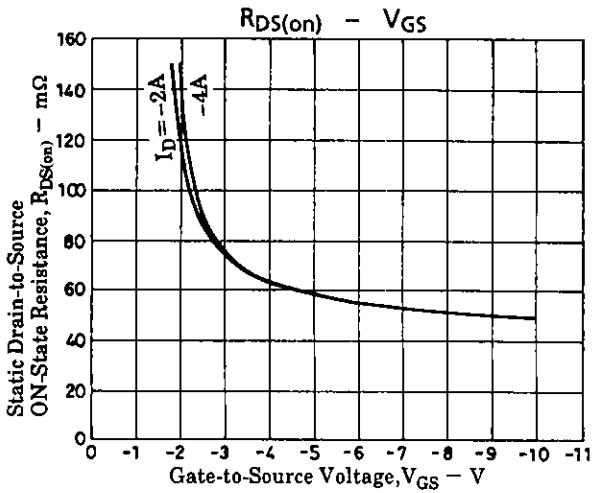
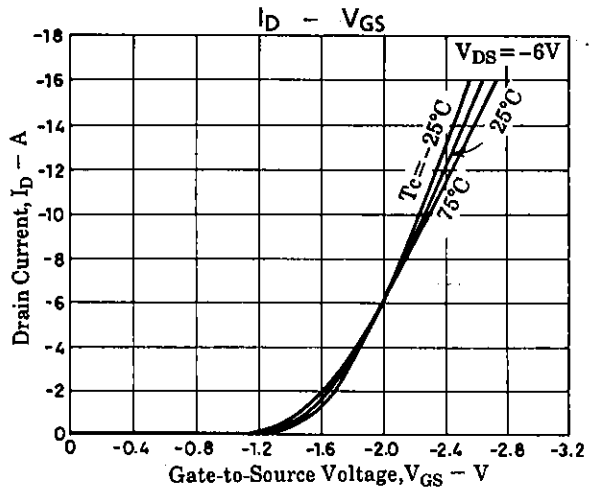
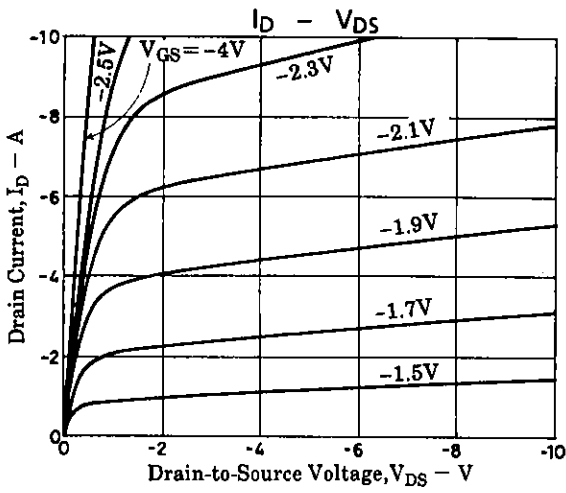
**Package Dimensions 2092B**

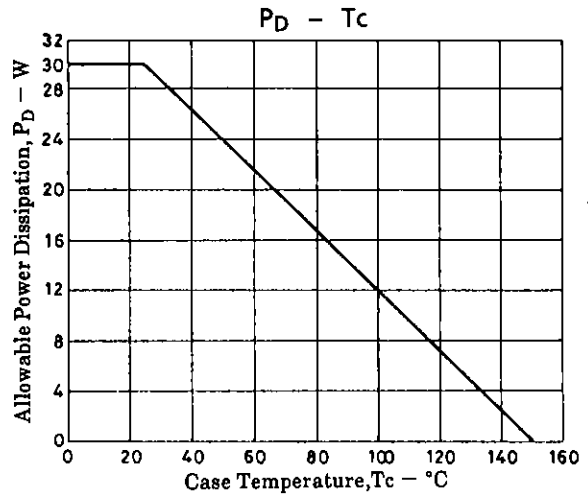
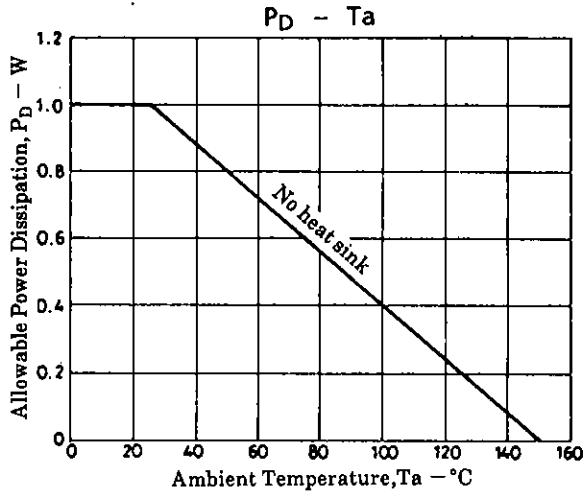
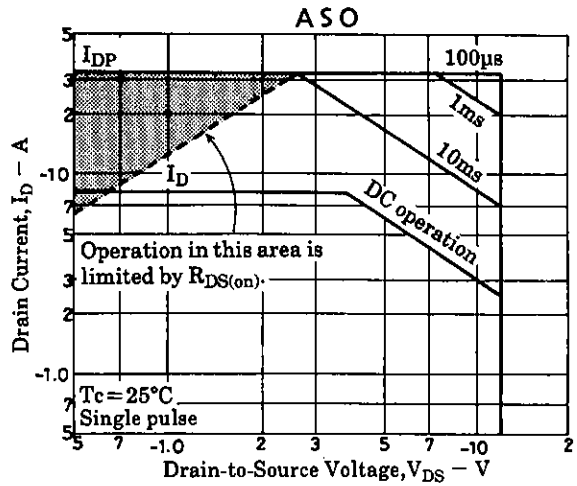
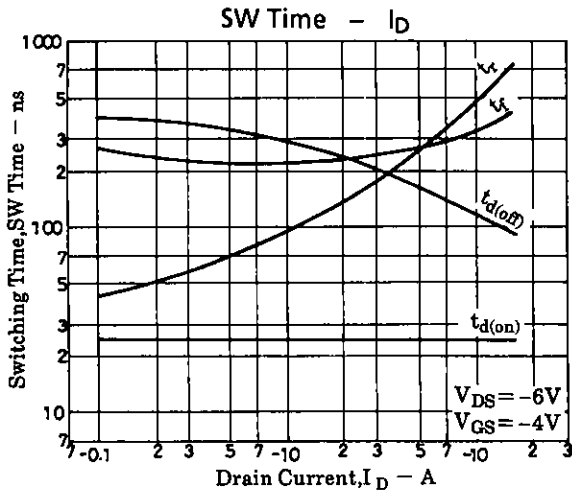
(unit: mm)



- 1: Gate
- 2: Drain
- 3: Source
- 4: Drain

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